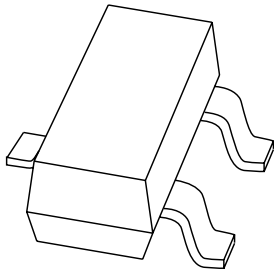


DATA SHEET



PMMT491A NPN BISS transistor

Product data sheet
Supersedes data of 2001 Jun 11

2004 Jan 13

NPN BISS transistor

PMMT491A

FEATURES

- High current (max. 1 A)
- Low collector-emitter saturation voltage ensures reduced power consumption.

APPLICATIONS

- Battery powered units where high current and low power consumption are important.

DESCRIPTION

NPN BISS (Breakthrough In Small Signal) transistor in a SOT23 plastic package. PNP complement: PMMT591A.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMMT491A	9A*

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

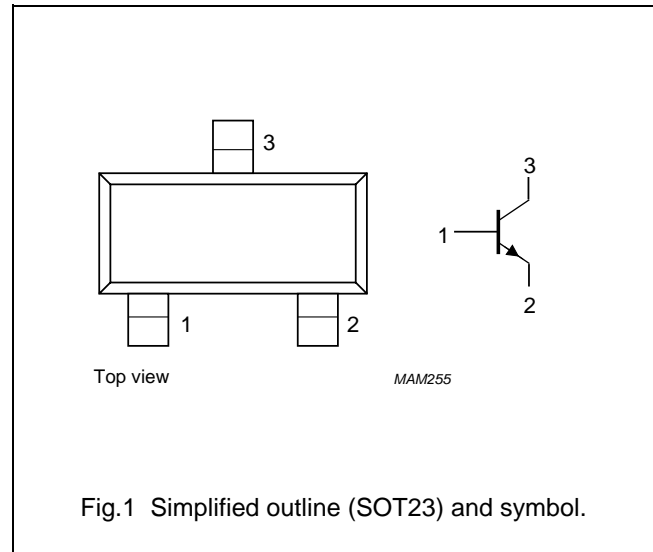


Fig.1 Simplified outline (SOT23) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PMMT491A	–	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	–	40	V
V _{CEO}	collector-emitter voltage	open base	–	40	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	2	A
I _{BM}	peak base current		–	1	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN BISS transistor

PMMT491A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

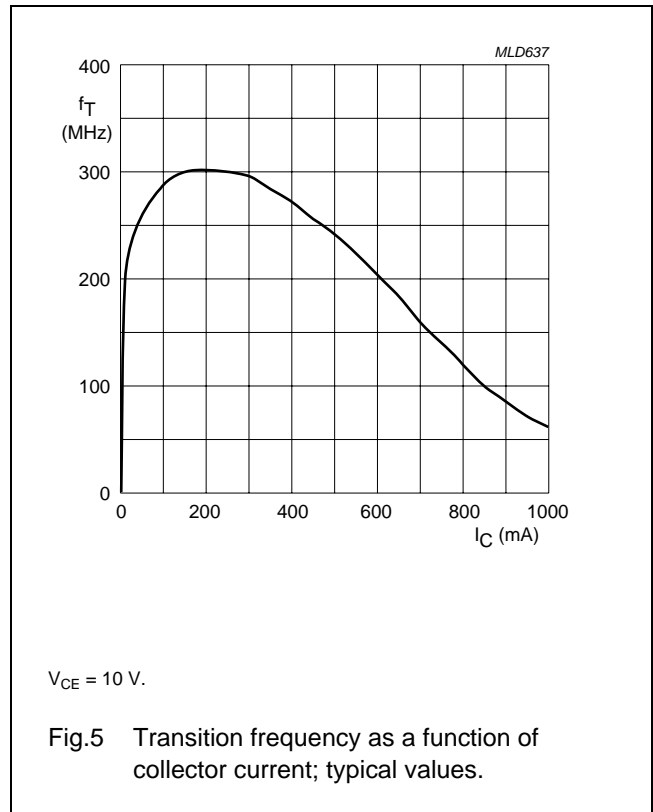
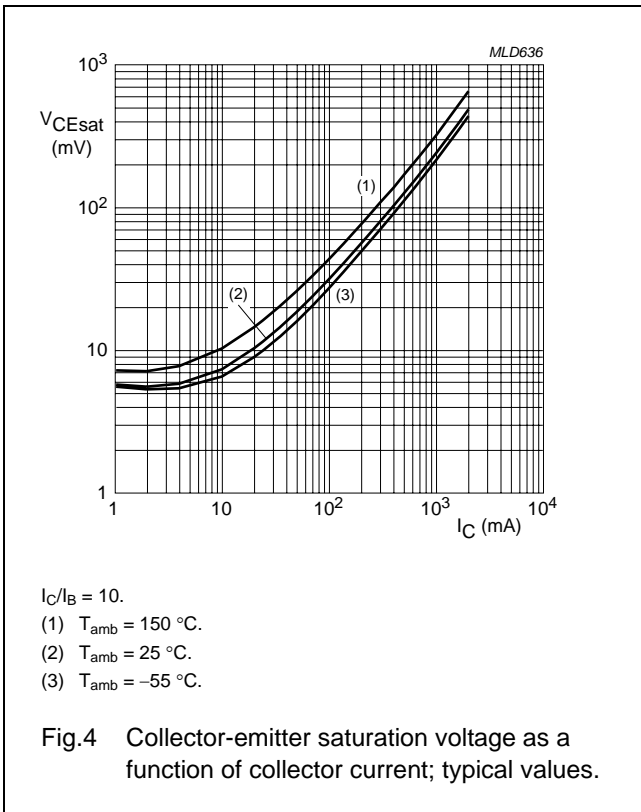
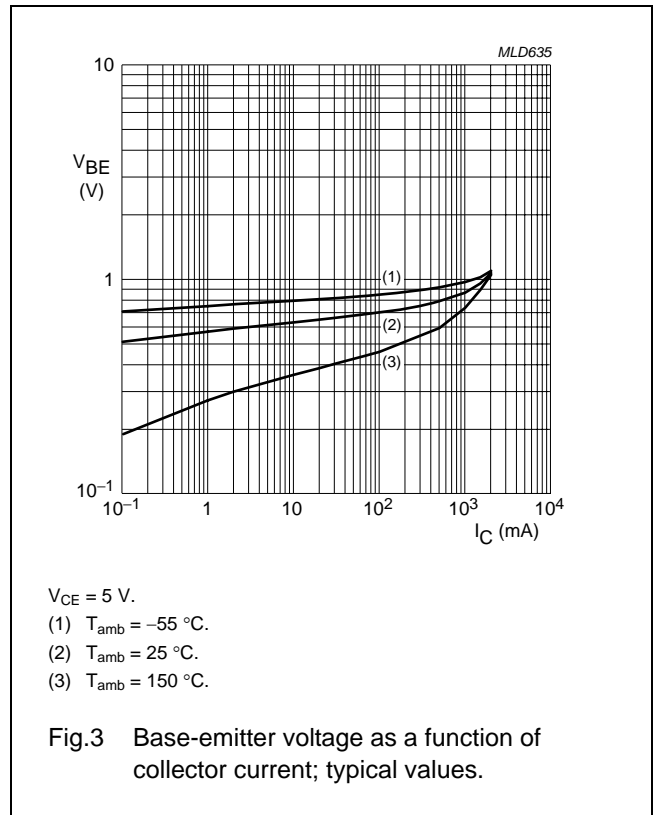
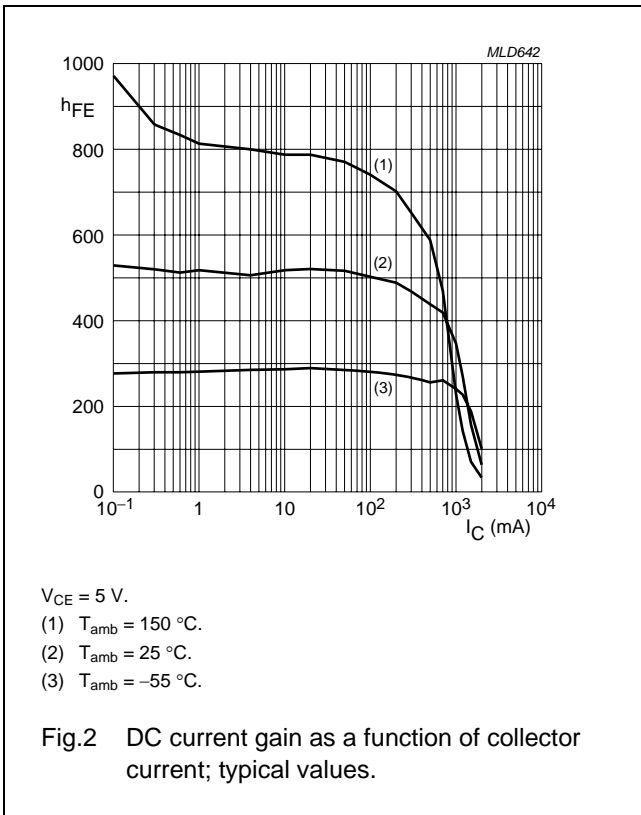
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	100	nA
I_{CEO}	collector cut-off current	$I_B = 0; V_{CE} = 30\text{ V}$	–	100	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; note 1 $I_C = 1\text{ mA}$ $I_C = 500\text{ mA}$ $I_C = 1\text{ A}$	300 300 200	– 900 –	
V_{CEsat}	collector-emitter saturation voltage	note 1 $I_C = 100\text{ mA}; I_B = 1\text{ mA}$ $I_C = 500\text{ mA}; I_B = 50\text{ mA}$ $I_C = 1\text{ A}; I_B = 100\text{ mA}$	– – –	200 300 500	mV mV mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$; note 1	–	1.2	V
V_{BE}	base-emitter voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$; note 1	–	1.1	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	10	pF
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	150	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

NPN BISS transistor

PMMT491A



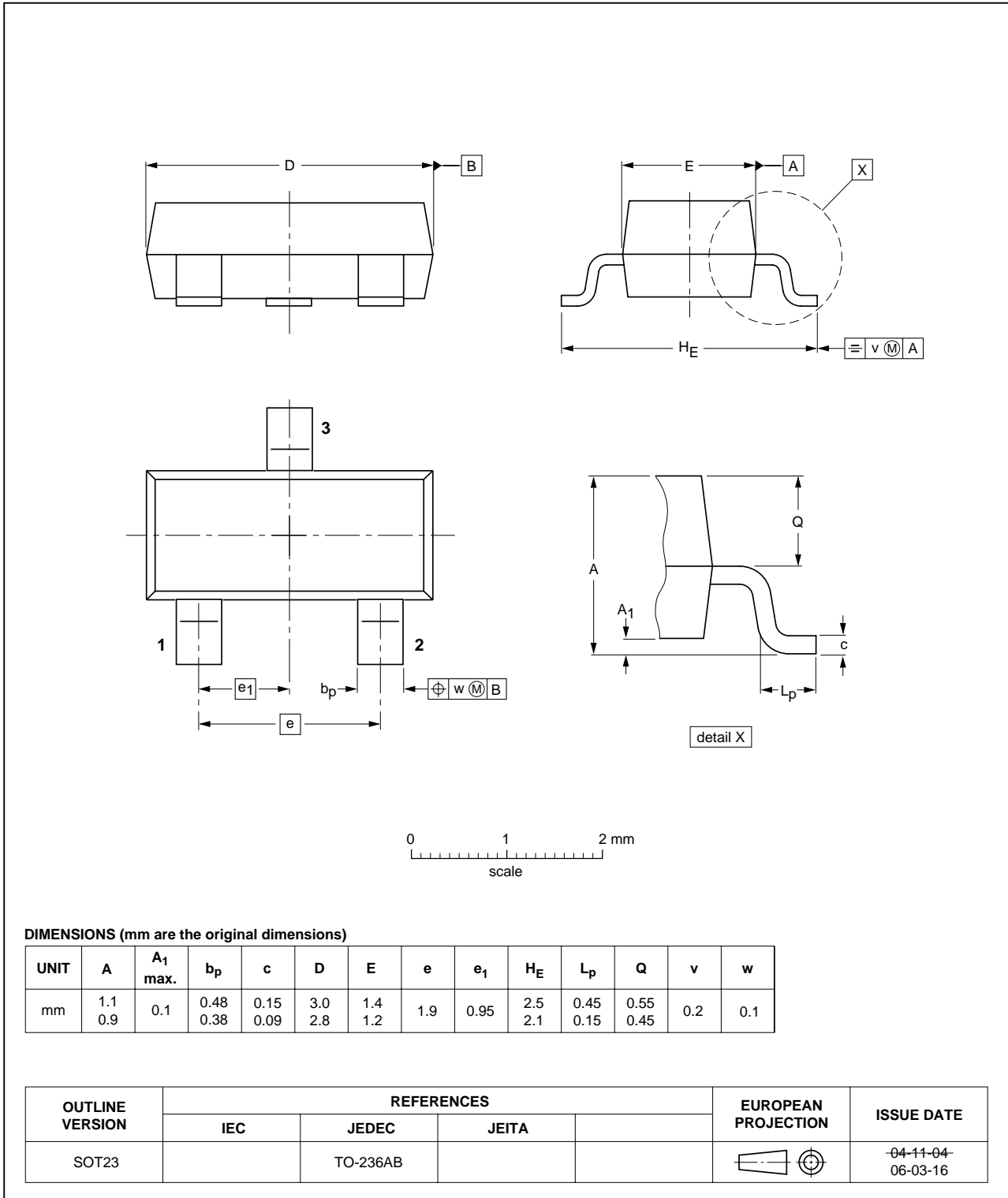
NPN BISS transistor

PMMT491A

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



NPN BISS transistor

PMMT491A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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